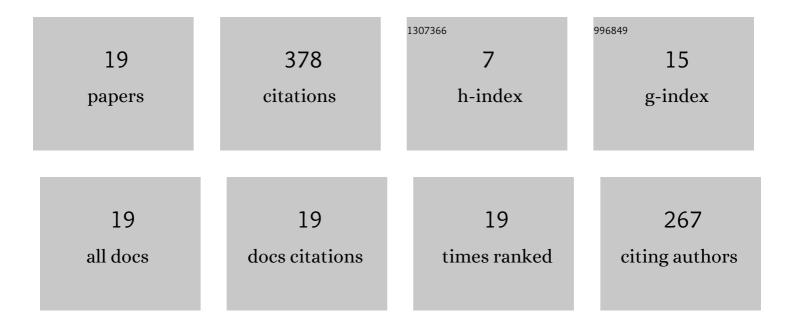
J Murray Gibson

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Evolution of coherent islands during strained-layer Volmer-Weber growth of Si on Ge(111). Physical Review B, 2001, 63, .	1.1	20
2	Control of Medium Range Order in Amorphous Silicon via Ion and Neutral Bombardment. Materials Research Society Symposia Proceedings, 2001, 664, 2731.	0.1	3
3	Medium-Range Order Structures of Amorphous Diamond-Like Carbon Films. Materials Research Society Symposia Proceedings, 2001, 675, 1.	0.1	2
4	Fluctuation Microscopy Studies of Medium-range Order Structures in Amorphous Tetrahedral Semiconductors. Materials Research Society Symposia Proceedings, 2000, 638, 1.	0.1	2
5	A Damage Model for Disordered Structures in Ion Irradiated Silicon. Materials Research Society Symposia Proceedings, 2000, 647, 1.	0.1	1
6	A Damage Model for Disordered Structures in Ion Irradiated Silicon. Materials Research Society Symposia Proceedings, 2000, 650, 1411.	0.1	1
7	TEM measurement of strain in coherent quantum heterostructures. Ultramicroscopy, 2000, 84, 225-233.	0.8	16
8	Dome-to-pyramid shape transition in Ge/Si islands due to strain relaxation by interdiffusion. Applied Physics Letters, 2000, 77, 1623-1625.	1.5	39
9	Strain Evolution in CoherentGe/Silslands. Physical Review Letters, 2000, 84, 1958-1961.	2.9	77
10	Direct measurement of strain in a Ge island on Si(001). Applied Physics Letters, 1999, 75, 46-48.	1.5	40
11	Strain in Coherent Ge Quantum Islands on Si Measured by Transmission Electron Microscopy. Materials Research Society Symposia Proceedings, 1999, 571, 49.	0.1	4
12	Identification of Shape Transitions in Coherent Ge/Si Islands Using Transmission Electron Microscopy. Materials Research Society Symposia Proceedings, 1999, 583, 137.	0.1	0
13	Shape Reversal of Ge/Si Domes to Pyramids Via Si-Ge Intermixing and Strain Reduction. Materials Research Society Symposia Proceedings, 1999, 583, 45.	0.1	0
14	In-Situ Transmission Electron Microscopy of Thin Film Growth. , 1997, , 149-171.		0
15	The effect of processing conditions on the structure of buried interfaces between silicon and silicon discon di dioxide. Materials Research Society Symposia Proceedings, 1996, 448, 303.	0.1	0
16	Visualization of Dynamic Near-Surface Processes. MRS Bulletin, 1994, 19, 38-43.	1.7	7
17	Elastic-displacement field of an isolated surface step. Physical Review B, 1994, 49, 13848-13858.	1.1	40
18	Dynamic observations of interface propagation during silicon oxidation. Physical Review Letters, 1992, 68, 1782-1785.	2.9	124

#	Article	IF	CITATIONS
19	Silicon Surface Morphology and the Reaction of Silicon with Oxygen. Materials Research Society Symposia Proceedings, 1992, 259, 87.	0.1	2